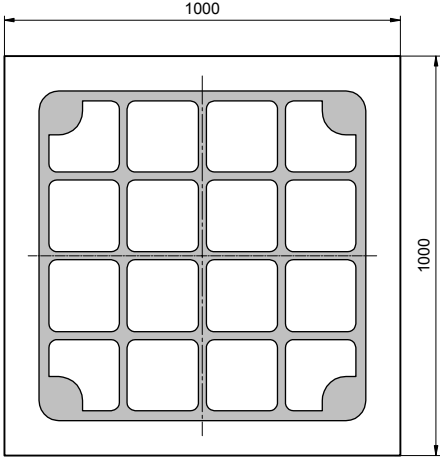


Radiation	Type	Technology	Electrodes
Red-orange	solderable	AlInGaP/GaAs	P (anode) up

 PoC-05	typ. dimensions (μm)	
	<u>typ. thickness</u> 260 (±20) μm <u>cathode</u> gold alloy, 1.5 μm <u>anode</u> gold alloy, 1.5 μm	

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 100 mA	V _F		1.9	2.3	V
Forward voltage	I _F = 300 mA	V _F		2.1		V
Reverse voltage	I _F = 10 μA	V _R	5			V
Radiant power ¹	I _F = 100 mA	Φ _e	4.6	6.0		mW
Radiant power ¹	I _F = 300 mA	Φ _e		16		mW
Luminous intensity ¹	I _F = 100 mA	I _V	225	290		mcd
Peak wavelength	I _F = 100 mA	λ _p	635	645	655	nm
Spectral bandwidth at 50%	I _F = 100 mA	Δλ _{0.5}		16		nm
Switching time	I _F = 100 mA	t _r , t _f		40		ns

¹Measured on bare chip on TO-18 header with EPIGAP equipment

Labeling

Type	Lot N°	Φ _e (typ) [mW]	V _F (typ) [V]	Quantity
ELC-645-11-05				

Packing: Chips on adhesive film with wire-bond side on top